Fan Ren

List of Publications by Year
in descending order

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		14124	18400
576	21,511	69	124
papers	citations	h-index	g-index

583	583	583	14397
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Digital biosensor for human cerebrospinal fluid detection with single-use sensing strips. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2022, 40, .	0.6	3
2	Band Alignment of Al₂O₃ on Î±-(Al_xGa_{1-x})₂O₃. ECS Journal of Solid State Science and Technology, 2022, 11, 025006.	0.9	4
3	Rapid SARS-CoV-2 diagnosis using disposable strips and a metal-oxide-semiconductor field-effect transistor platform. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2022, 40, 023204.	0.6	4
4	Variable temperature probing of minority carrier transport and optical properties in p-Ga2O3. APL Materials, 2022, 10, .	2.2	12
5	Deep level defect states in Î²-, Î±-, and É›-Ga2O3 crystals and films: Impact on device performance. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, .	0.9	35
6	Exfoliated and bulk Î²-gallium oxide electronic and photonic devices. , 2022, 1, 100001.		6
7	Thermo-mechanical aspects of gamma irradiation effects on GaN HEMTs. Applied Physics Letters, 2022, 120, .	1.5	9
8	Growth and characterization of (Sc₂O₃)_x(Ga₂O₃)_{1â^'x} by molecular beam epitaxy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, 043403.	0.9	1
9	Impact of radiation and electron trapping on minority carrier transport in p-Ga2O3. Applied Physics Letters, 2022, 120, .	1.5	9
10	Nanoscale Stress Localization Effects on the Radiation Susceptibility of GaN Highâ€Mobility Transistors. Physica Status Solidi - Rapid Research Letters, 2022, 16, .	1.2	5
11	Thermal effects in Ga2O3 rectifiers and MOSFETs borrowing from GaN. , 2022, , 441-467.		0
12	Annealing temperature dependence of band alignment of NiO/Î²-Ga₂O₃. Journal Physics D: Applied Physics, 2022, 55, 385105.	1.3	22
13	Color perceptibility and validity of silicon carbideâ€“based protective coatings for dental ceramics. Journal of Prosthetic Dentistry, 2021, , .	1.1	0
14	Novel Coatings to Minimize Corrosion of Titanium in Oral Biofilm. Materials, 2021, 14, 342.	1.3	6
15	Design of Ga2O3 modulation doped field effect transistors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	0.9	13
16	Artificial Neuron and Synapse Devices Based on 2D Materials. Small, 2021, 17, e2100640.	5.2	75
17	Vertical Î²-Ga₂O₃Schottky rectifiers with 750 V reverse breakdown voltage at 600 K. Journal Physics D: Applied Physics, 2021, 54, 305103.	1.3	13
18	Fast SARS-CoV-2 virus detection using disposable cartridge strips and a semiconductor-based biosensor platform. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2021, 39, 033202.	0.6	14

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19	Reviewâ€"Radiation Damage in Wide and Ultra-Wide Bandgap Semiconductors. ECS Journal of Solid State Science and Technology, 2021, 10, 055008.	0.9	56
20	Experimental estimation of electronâ€"hole pair creation energy in Î² -Ga2O3. Applied Physics Letters, 2021, 118, .	1.5	26
21	Electron beam probing of non-equilibrium carrier dynamics in 18â€‰MeV alpha particle- and 10â€‰MeV proton-irradiated Si-doped Î² -Ga2O3 Schottky rectifiers. Applied Physics Letters, 2021, 118, .	1.5	10
22	Neuromorphic Devices: Artificial Neuron and Synapse Devices Based on 2D Materials (Small 20/2021). Small, 2021, 17, 2170092.	5.2	0
23	Effects of Downstream Plasma Exposure on Î²-Ga₂O₃ Rectifiers. ECS Journal of Solid State Science and Technology, 2021, 10, 065005.	0.9	4
24	A Review: Microstructural and Phase Evolution in Alloys during Extended Plastic Deformation. Jom, 2021, 73, 2212-2224.	0.9	4
25	Crystal orientation dependence of deep level spectra in proton irradiated bulk Î²-Ga2O3. Journal of Applied Physics, 2021, 130, .	1.1	12
26	Qualitative Analysis of Remineralization Capabilities of Bioactive Glass (NovaMin) and Fluoride on Hydroxyapatite (HA) Discs: An In Vitro Study. Materials, 2021, 14, 3813.	1.3	9
27	Reviewâ€"Opportunities in Single Event Effects in Radiation-Exposed SiC and GaN Power Electronics. ECS Journal of Solid State Science and Technology, 2021, 10, 075004.	0.9	13
28	OH-Si complex in hydrogenated n-typeÎ²-Ga2O3:Si. Applied Physics Letters, 2021, 119, .	1.5	14
29	Nanostructured Surfaces to Promote Osteoblast Proliferation and Minimize Bacterial Adhesion on Titanium. Materials, 2021, 14, 4357.	1.3	12
30	Temperature dependent performance of ITO Schottky contacts on Î²-Ga2O3. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	0.9	12
31	In Vitro Corrosion of SiC-Coated Anodized Ti Nano-Tubular Surfaces. Journal of Functional Biomaterials, 2021, 12, 52.	1.8	2
32	On the nature of photosensitivity gain in Ga2O3 Schottky diode detectors: Effects of hole trapping by deep acceptors. Journal of Alloys and Compounds, 2021, 879, 160394.	2.8	23
33	Nitrogen ion-implanted resistive regions for edge termination of vertical Ga2O3 rectifiers. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, 063405.	0.9	8
34	Diffusion of dopants and impurities in Î²-Ga2O3. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	0.9	26
35	Effect of probe geometry during measurement of >100â€‰A Ga2O3 vertical rectifiers. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	0.9	30
36	Thermal Stability of Transparent ITO/n-Ga₂O₃/n+-Ga₂O₃/ITO Rectifiers. ECS Journal of Solid State Science and Technology, 2021, 10, 115005.	0.9	4

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37	Al Composition Dependence of Band Offsets for SiO₂ on Î±-(Al_xGa_{1â^'x})₂O₃. ECS Journal of Solid State Science and Technology, 2021, 10, 113007.	0.9	6
38	1â€‰GeV proton damage in Î²-Ga2O3. Journal of Applied Physics, 2021, 130, .	1.1	7
39	Temperature dependence of cathodoluminescence emission in irradiated Si-doped Î²-Ga2O3. AIP Advances, 2021, 11, .	0.6	9
40	Reviewâ€"Opportunities for Rapid, Sensitive Detection of Troponin and Cerebral Spinal Fluid Using Semiconductor Sensors. Journal of the Electrochemical Society, 2020, 167, 037507.	1.3	7
41	A Two-Electrode, Double-Pulsed Sensor Readout Circuit for Cardiac Troponin I Measurement. IEEE Transactions on Biomedical Circuits and Systems, 2020, 14, 1362-1370.	2.7	6
42	Impact of electron injection on carrier transport and recombination in unintentionally doped GaN. Journal of Applied Physics, 2020, 128, .	1.1	7
43	Demonstration of a SiC Protective Coating for Titanium Implants. Materials, 2020, 13, 3321.	1.3	24
44	Rapid Electrochemical Detection for SARS-CoV-2 and Cardiac Troponin I Using Low-Cost, Disposable and Modular Biosensor System. , 2020, , .		5
45	Effect of pH Cycling Frequency on Glassâ€"Ceramic Corrosion. Materials, 2020, 13, 3655.	1.3	5
46	Titanium Corrosion in Peri-Implantitis. Materials, 2020, 13, 5488.	1.3	16
47	Hydroxyapatite Formation on Coated Titanium Implants Submerged in Simulated Body Fluid. Materials, 2020, 13, 5593.	1.3	7
48	Band offset determination for amorphous Al2O3 deposited on bulk AlN and atomic-layer epitaxial AlN on sapphire. Applied Physics Letters, 2020, 117, 182103.	1.5	5
49	The Galvanic Effect of Titanium and Amalgam in the Oral Environment. Materials, 2020, 13, 4425.	1.3	0
50	Photosensitivity of Ga2O3 Schottky diodes: Effects of deep acceptor traps present before and after neutron irradiation. APL Materials, 2020, 8, .	2.2	30
51	Effect of Electron Injection on Minority Carrier Transport in 10 MeV Proton Irradiated Î²-Ga₂O₃ Schottky Rectifiers. ECS Journal of Solid State Science and Technology, 2020, 9, 045018.	0.9	12
52	Alpha Particle Irradiation of High Aluminum Content AlGan Polarization Doped Field Effect Transistors. ECS Journal of Solid State Science and Technology, 2020, 9, 035008.	0.9	2
53	AlGaN/GaN heterostructure based Pt nanonetwork Schottky diode with water-blocking layer. Sensors and Actuators B: Chemical, 2020, 317, 128234.	4.0	7
54	In Situ Transmission Electron Microscopy Observations of Forward Bias Degradation of Vertical Geometry Î²-Ga₂O₃ Rectifiers. ECS Journal of Solid State Science and Technology, 2020, 9, 055008.	0.9	6

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55	Annealing Effects on the Band Alignment of ALD SiO₂ on (In_xGa_{1â^'x})₂O₃ for x = 0.25â€“0.74. ECS Journal of Solid State Science and Technology, 2020, 9, 045001.	0.9	0
56	Annealing and N2 Plasma Treatment to Minimize Corrosion of SiC-Coated Glass-Ceramics. Materials, 2020, 13, 2375.	1.3	5
57	Novel Coatings to Minimize Bacterial Adhesion and Promote Osteoblast Activity for Titanium Implants. Journal of Functional Biomaterials, 2020, 11, 42.	1.8	18
58	Novel Coating to Minimize Corrosion of Glass-Ceramics for Dental Applications. Materials, 2020, 13, 1215.	1.3	16
59	Dissolution activation energy of a fluorapatite glass-ceramic veneer for dental applications. Materials Science and Engineering C, 2020, 111, 110802.	3.8	6
60	Asymmetrical Contact Geometry to Reduce Forward-Bias Degradation in Î²-Ga2O3 Rectifiers. ECS Journal of Solid State Science and Technology, 2020, 9, 035007.	0.9	10
61	Changes in band alignment during annealing at 600â€‰Â°C of ALD Al2O3 on (InxGa1â€‰â^'â€‰x)2O3 for xâ€‰=â€‰0.25â€“0.7 Journal of Applied Physics, 2020, 127, 105701.	1.1	6
62	In Situ Observation of Î²-Ga₂O₃ Schottky Diode Failure Under Forward Biasing Condition. IEEE Transactions on Electron Devices, 2020, 67, 3056-3061.	1.6	16
63	Plasma etching of wide bandgap and ultrawide bandgap semiconductors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	0.9	23
64	Pulsed fast reactor neutron irradiation effects in Si doped n-type Î²-Ga₂O₃. Journal Physics D: Applied Physics, 2020, 53, 274001.	1.3	22
65	Nanosensor networks for health-care applications. , 2020, , 405-417.		3
66	High temperature operation to 500â€‰Â°C of AlGaN graded polarization-doped field-effect transistors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2020, 38, .	0.6	2
67	Role of hole trapping by deep acceptors in electron-beam-induced current measurements in Î²-Ga₂O₃ vertical rectifiers. Journal Physics D: Applied Physics, 2020, 53, 495108.	1.3	16
68	Anti-Bacterial Properties and Biocompatibility of Novel SiC Coating for Dental Ceramic. Journal of Functional Biomaterials, 2020, 11, 33.	1.8	19
69	(Invited) Fabrication and Characterization of High Power Ga2O3 Based Diodes. ECS Meeting Abstracts, 2020, MA2020-01, 1326-1326.	0.0	1
70	A Pulsed Electrochemistry Readout IC for Single Transistor-based Biosensor. , 2020, , .		0
71	Design and implementation of floating field ring edge termination on vertical geometry Î²-Ga2O3 rectifiers. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, 063414.	0.9	6
72	Prefaceâ€”JSS Focus Issue on Solid-State Materials and Devices for Biological and Medical Applications. ECS Journal of Solid State Science and Technology, 2020, 9, 110001.	0.9	0

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73	Diodes 1. Springer Series in Materials Science, 2020, , 661-688.	0.4	0
74	Opportunities and Challenges in MOCVD of Î²-Ga₂O₃ for Power Electronic Devices. Selected Topics in Electornics and Systems, 2020, , 127-144.	0.2	0
75	Prefaceâ€"JSS Focus Issue on Gallium Oxide Based Materials and Devices II. ECS Journal of Solid State Science and Technology, 2020, 9, 060001.	0.9	2
76	Valence band offsets for ALD SiO2 and Al2O3 on (InxGa1â^'x)2O3 for x = 0.25â€"0.74. APL Materials, 2019, 7, .	2.2	14
77	The role of annealing ambient on diffusion of implanted Si in Î²-Ga2O3. AIP Advances, 2019, 9, .	0.6	27
78	Hydrogen plasma treatment of Î² -Ga2O3: Changes in electrical properties and deep trap spectra. Applied Physics Letters, 2019, 115, .	1.5	39
79	Band Alignment of Atomic Layer Deposited SiO2 and Al2O3 on (AlxGa1-x)2O3 for x = 0.2-0.65. ECS Journal of Solid State Science and Technology, 2019, 8, P351-P356.	0.9	12
80	A Reconfigurable, Pulse-shaping Potentiometric Readout System for Bio-Sensing Transistors. , 2019, 2019, 5761-5764.		5
81	Effects of Hydrogen Plasma Treatment Condition on Electrical Properties of Î²-Ga₂O₃. ECS Journal of Solid State Science and Technology, 2019, 8, P661-P666.	0.9	7
82	Antibacterial Properties of Charged TiN Surfaces for Dental Implant Application. ChemistrySelect, 2019, 4, 9185-9189.	0.7	10
83	Forward bias degradation and thermal simulations of vertical geometry Î²-Ga2O3 Schottky rectifiers. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2019, 37, .	0.6	17
84	Band Offsets of Insulating & Semiconducting Oxides on (Al_xGa_{1-x})O₃. ECS Transactions, 2019, 92, 79-88.	0.3	6
85	Electro-Thermal Analysis and Edge Termination Techniques of High Current Î²-Ga2 O3 Schottky Rectifiers. , 2019, , .		0
86	Diffusion of implanted Ge and Sn in Î²-Ga2O3. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2019, 37, .	0.6	22
87	Effect of thermal annealing for W/Î²-Ga2O3 Schottky diodes up to 600â€‰Â°C. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2019, 37, .	0.6	17
88	Radiation damage effects in Ga₂O₃ materials and devices. Journal of Materials Chemistry C, 2019, 7, 10-24.	2.7	154
89	Electron injection-induced effects in Si-doped Î²-Ga2O3. AIP Advances, 2019, 9, .	0.6	15
90	Electrical Properties, Deep Trap and Luminescence Spectra in Semi-Insulating, Czochralski Î²-Ga₂O₃ (Mg). ECS Journal of Solid State Science and Technology, 2019, 8, Q3019-Q3023.	0.9	41

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91	Device processing and junction formation needs for ultra-high power Ga2O3 electronics. MRS Communications, 2019, 9, 77-87.	0.8	24
92	Switching Behavior and Forward Bias Degradation of 700V, 0.2A, Î²-Ga₂O₃Vertical Geometry Rectifiers. ECS Journal of Solid State Science and Technology, 2019, 8, Q3028-Q3033.	0.9	18
93	Implementation of a 900ÂV Switching Circuit for High Breakdown Voltage Î²-Ga₂O₃ Schottky Diodes. ECS Journal of Solid State Science and Technology, 2019, 8, Q3229-Q3234.	0.9	18
94	Fast Cerebrospinal Fluid Detection Using Inexpensive Modular Packaging with Disposable Testing Strips. Journal of the Electrochemical Society, 2019, 166, B708-B712.	1.3	7
95	Vertical geometry 33.2 A, 4.8 MWâ€‰cm2 Ga2O3 field-plated Schottky rectifier arrays. Applied Physics Letters, 2019, 114, .	1.5	50
96	Defects at the surface of Î²-Ga2O3 produced by Ar plasma exposure. APL Materials, 2019, 7, .	2.2	36
97	Will surface effects dominate in quasi-two-dimensional gallium oxide for electronic and photonic devices?. Nanoscale Horizons, 2019, 4, 1251-1255.	4.1	10
98	Comparison of Dual-Stack Dielectric Field Plates on Î²-Ga₂O₃ Schottky Rectifiers. ECS Journal of Solid State Science and Technology, 2019, 8, Q3221-Q3225.	0.9	30
99	Thermoreflectance Temperature Mapping of Ga2O3 Schottky Barrier Diodes. ECS Transactions, 2019, 89, 3-7.	0.3	7
100	Demonstration of SiO₂/SiCâ€based protective coating for dental ceramic prostheses. Journal of the American Ceramic Society, 2019, 102, 6591-6599.	1.9	12
101	Operation Up to 500 Â°C of Al_{0.85}Ga_{0.15}N/Al_{0.7}Ga_{0.3}N High Electron Mobility Transistors. IEEE Journal of the Electron Devices Society, 2019, 7, 444-452.	1.2	36
102	Damage Recovery and Dopant Diffusion in Si and Sn Ion Implanted Î²-Ga₂O₃. ECS Journal of Solid State Science and Technology, 2019, 8, Q3133-Q3139.	0.9	29
103	Reverse Breakdown in Large Area, Field-Plated, Vertical Î²-Ga₂O₃Rectifiers. ECS Journal of Solid State Science and Technology, 2019, 8, Q3159-Q3164.	0.9	36
104	Deep traps and persistent photocapacitance in Î²-(Al0.14 Ga0.86)2O3/Ga2O3 heterojunctions. Journal of Applied Physics, 2019, 125, .	1.1	2
105	Heterojunction Bipolar Transistor: 2D Material-Based Vertical Double Heterojunction Bipolar Transistors with High Current Amplification (Adv. Electron. Mater. 3/2019). Advanced Electronic Materials, 2019, 5, 1970015.	2.6	2
106	Valence and Conduction Band Offsets for InN and III-Nitride Ternary Alloys on (â^'201) Bulk Î²-Ga₂O₃. ECS Journal of Solid State Science and Technology, 2019, 8, Q3154-Q3158.	0.9	15
107	Thermal Simulations of High Current Î²-Ga₂O₃ Schottky Rectifiers. ECS Journal of Solid State Science and Technology, 2019, 8, Q3195-Q3201.	0.9	31
108	⁶⁰Co Gamma Ray Damage in Homoepitaxial Î²-Ga₂O₃Schottky Rectifiers. ECS Journal of Solid State Science and Technology, 2019, 8, Q3041-Q3045.	0.9	18

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109	Valence- and Conduction-Band Offsets for Atomic-Layer-Deposited Al2O3 on (010) (Al0.14Ga0.86)2O3. Journal of Electronic Materials, 2019, 48, 1568-1573.	1.0	19
110	Impact of Electron Injection and Temperature on Minority Carrier Transport in Alpha-Irradiated ÃŸ-Ga₂O₃ Schottky Rectifiers. ECS Journal of Solid State Science and Technology, 2019, 8, Q3050-Q3053.	0.9	14
111	Comprehensive analysis of laserscanner validity used for measurement of wear. Journal of Oral Rehabilitation, 2019, 46, 503-510.	1.3	2
112	Effect of Annealing on the Band Alignment of ALD SiO₂ on (Al_xGa_{1-x})₂O₃ for x = 0.2 - 0.65. ECS Journal of Solid State Science and Technology, 2019, 8, P751-P756.	0.9	6
113	Annealing of Proton and Alpha Particle Damage in Au-W/Î²-Ga2O3 Rectifiers. ECS Journal of Solid State Science and Technology, 2019, 8, P799-P804.	0.9	4
114	Opportunities and Challenges in MOCVD of Î²Ga₂O₃ for Power Electronic Devices. International Journal of High Speed Electronics and Systems, 2019, 28, 1940007.	0.3	7
115	Optimization of Edge Termination Techniques for Î²-Ga₂O₃ Schottky Rectifiers. ECS Journal of Solid State Science and Technology, 2019, 8, Q234-Q239.	0.9	16
116	Temperature-Dependent Electrical Characteristics of Î²-Ga₂O₃Diodes with W Schottky Contacts up to 500Â°C. ECS Journal of Solid State Science and Technology, 2019, 8, Q3007-Q3012.	0.9	56
117	Valence and conduction band offsets for sputtered AZO and ITO on (010) (Al_{0.14}Ga_{0.86})₂O₃. Semiconductor Science and Technology, 2019, 34, 025006.	1.0	8
118	2D Materialâ€Based Vertical Double Heterojunction Bipolar Transistors with High Current Amplification. Advanced Electronic Materials, 2019, 5, 1800745.	2.6	26
119	Defect States Determining Dynamic Trapping-Detrapping in Î²-Ga₂O₃ Field-Effect Transistors. ECS Journal of Solid State Science and Technology, 2019, 8, Q3013-Q3018.	0.9	30
120	Dynamic Switching Characteristics of 1 A Forward Current $oldsymbol{eta}$ -Ga₂O₃ Rectifiers. IEEE Journal of the Electron Devices Society, 2019, 7, 57-61.	1.2	36
121	Effect of Deposition Method on Valence Band Offsets of SiO₂ and Al₂O₃ on (Al_{0.14}Ga_{0.86})₂O₃. ECS Journal of Solid State Science and Technology, 2019, 8, Q3001-Q3006.	0.9	10
122	Band alignments of dielectrics on (â¯ 201) Î²-Ga2O3. , 2019, , 287-311.		3
123	DC and dynamic switching characteristics of field-plated vertical geometry [beta]-Ga2O3 rectifiers. , 2019, , .		2
124	Moisture Insensitive PMMA Coated Pt-AlGaN/GaN Diode Hydrogen Sensor and Its Thermal Stability. ECS Journal of Solid State Science and Technology, 2018, 7, Q3009-Q3013.	0.9	10
125	Trapping Phenomena in InAlN/GaN High Electron Mobility Transistors. ECS Journal of Solid State Science and Technology, 2018, 7, Q1-Q7.	0.9	11
126	Point defect induced degradation of electrical properties of Ga2O3 by 10â€‰MeV proton damage. Applied Physics Letters, 2018, 112, .	1.5	98

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127	A review of Ga2O3 materials, processing, and devices. Applied Physics Reviews, 2018, 5, .	5.5	1,816
128	10 MeV proton damage in Î²-Ga2O3 Schottky rectifiers. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2018, 36, .	0.6	31
129	Effects of fluorine incorporation into Î²-Ga2O3. Journal of Applied Physics, 2018, 123, .	1.1	27
130	Effect of 1.5â€‰MeV electron irradiation on Î²-Ga2O3 carrier lifetime and diffusion length. Applied Physics Letters, 2018, 112, .	1.5	55
131	AlGaN/GaN Heterostructure Based Schottky Diode Sensors with ZnO Nanorods for Environmental Ammonia Monitoring Applications. ECS Journal of Solid State Science and Technology, 2018, 7, Q3020-Q3024.	0.9	24
132	Randomized clinical study of wear of enamel antagonists against polished monolithic zirconia crowns. Journal of Dentistry, 2018, 68, 19-27.	1.7	73
133	A comparative study of wet etching and contacts on <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si1.gif" overflow="scroll"><mml:mrow><mml:mo>(</mml:mo><mml:mrow><mml:mover) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 497 Td and (010) oriented Î²-Ga2O3. Journal of Alloys and Compounds, 2018, 731, 118-125.	2.8	55
134	Novel Testing for Corrosion of Glass-Ceramics for Dental Applications. Journal of Dental Research, 2018, 97, 296-302.	2.5	16
135	Perspective: Ga2O3 for ultra-high power rectifiers and MOSFETS. Journal of Applied Physics, 2018, 124, .	1.1	416
136	Band alignment of atomic layer deposited SiO2 on (010) (Al0.14Ga0.86)2O3. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2018, 36, .	0.6	18
137	Band Offsets for Atomic Layer Deposited HfSiO₄ on (Al_{0.14}Ga_{0.86})₂O₃. ECS Journal of Solid State Science and Technology, 2018, 7, P519-P523.	0.9	9
138	Effect of surface treatments on electrical properties of Î²-Ga2O3. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2018, 36, .	0.6	49
139	Electrical properties of bulk semi-insulating Î²-Ga2O3 (Fe). Applied Physics Letters, 2018, 113, .	1.5	77
140	Valence band offsets for CuI on (-201) bulk Ga2O3 and epitaxial (010) (Al0.14Ga0.86)2O3. Applied Physics Letters, 2018, 113, .	1.5	17
141	Hole traps and persistent photocapacitance in proton irradiated Î²-Ga2O3 films doped with Si. APL Materials, 2018, 6, .	2.2	73
142	Effect of proton irradiation energy on SiNx/AlGaN/GaN metal-insulator semiconductor high electron mobility transistors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2018, 36, .	0.6	15
143	Defects responsible for charge carrier removal and correlation with deep level introduction in irradiated Î²-Ga2O3. Applied Physics Letters, 2018, 113, .	1.5	62
144	2300V Reverse Breakdown Voltage Ga₂O₃Schottky Rectifiers. ECS Journal of Solid State Science and Technology, 2018, 7, Q92-Q96.	0.9	169

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145	Hydrogen Sensing Characteristics of Pt Schottky Diodes on () and (010) Ga₂O₃Single Crystals. ECS Journal of Solid State Science and Technology, 2018, 7, Q3180-Q3182.	0.9	21
146	Effect of alpha-particle irradiation dose on SiNx/AlGaN/GaN metalâ€“insulator semiconductor high electron mobility transistors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2018, 36, .	0.6	7
147	Zika virus detection using antibody-immobilized disposable cover glass and AlGaN/GaN high electron mobility transistors. Applied Physics Letters, 2018, 113, .	1.5	27
148	Diffusion length of non-equilibrium minority charge carriers in Î²-Ga2O3 measured by electron beam induced current. Journal of Applied Physics, 2018, 123, .	1.1	50
149	Eighteen mega-electron-volt alpha-particle damage in homoepitaxial Î²-Ga2O3 Schottky rectifiers. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2018, 36, .	0.6	18
150	Ga2O3 Schottky rectifiers with 1 ampere forward current, 650 V reverse breakdown and 26.5 MW.cm-2 figure-of-merit. AIP Advances, 2018, 8, .	0.6	73
151	Vertical Geometry, 2-A Forward Current Ga₂O₃ Schottky Rectifiers on Bulk Ga₂O₃ Substrates. IEEE Transactions on Electron Devices, 2018, 65, 2790-2796.	1.6	41
152	Current relaxation analysis in AlGaN/GaN high electron mobility transistors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2017, 35, .	0.6	12
153	Temperature-Dependent Characteristics of Ni/Au and Pt/Au Schottky Diodes on Î²-Ga₂O₃. ECS Journal of Solid State Science and Technology, 2017, 6, P68-P72.	0.9	76
154	Effect of deposition conditions and composition on band offsets in atomic layer deposited HfxSi1â^'xOy on InGaZnO4. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2017, 35, .	0.6	9
155	Energy band offsets of dielectrics on InGaZnO4. Applied Physics Reviews, 2017, 4, .	5.5	65
156	High reverse breakdown voltage Schottky rectifiers without edge termination on Ga2O3. Applied Physics Letters, 2017, 110, .	1.5	149
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